

MJ11028, MJ11030, MJ11032 (NPN) MJ11029, MJ11033 (PNP)



ON Semiconductor®

<http://onsemi.com>

High-Current Complementary Silicon Power Transistors

High-Current Complementary Silicon Power Transistors are for use as output devices in complementary general purpose amplifier applications.

Features

- High DC Current Gain – $h_{FE} = 1000$ (Min) @ $I_C = 25$ Adc
 $h_{FE} = 400$ (Min) @ $I_C = 50$ Adc
- Curves to 100 A (Pulsed)
- Diode Protection to Rated I_C
- Monolithic Construction with Built-In Base-Emitter Shunt Resistor
- Junction Temperature to +200°C
- Pb-Free Packages are Available*

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage MJ11028/29 MJ11030 MJ11032/33	V_{CEO}	60 90 120	Vdc
Collector-Base Voltage MJ11028/29 MJ11030 MJ11032/33	V_{CBO}	60 90 120	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous – Peak (Note 1)	I_C	50 100	Adc
Base Current – Continuous	I_B	2.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate Above 25°C @ $T_C = 100^\circ\text{C}$	P_D	300 1.71	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +200	°C

THERMAL CHARACTERISTICS

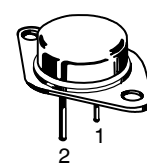
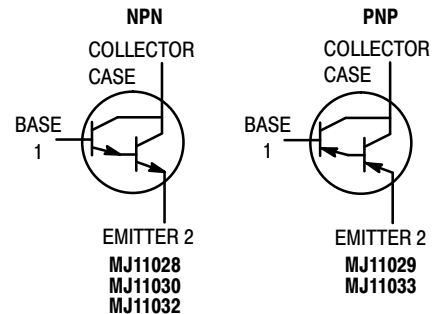
Characteristic	Symbol	Max	Unit
Maximum Lead Temperature for Soldering Purposes for ≤ 10 seconds	T_L	275	°C
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.58	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5 μs , Duty Cycle $\leq 10\%$.

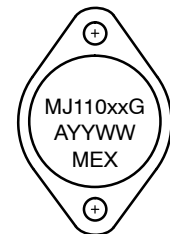
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

50 AMPERE COMPLEMENTARY DARLINGTON POWER TRANSISTORS 60 – 120 VOLTS 300 WATTS



TO-204 (TO-3)
CASE 197A
STYLE 1

MARKING DIAGRAM



MJ110xx = Device Code
xx = 28, 29, 30, 32, 33
G = Pb-Free Package
A = Location Code
YY = Year
WW = Work Week
MEX = Country of Origin

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

MJ11028, MJ11030, MJ11032 (NPN)

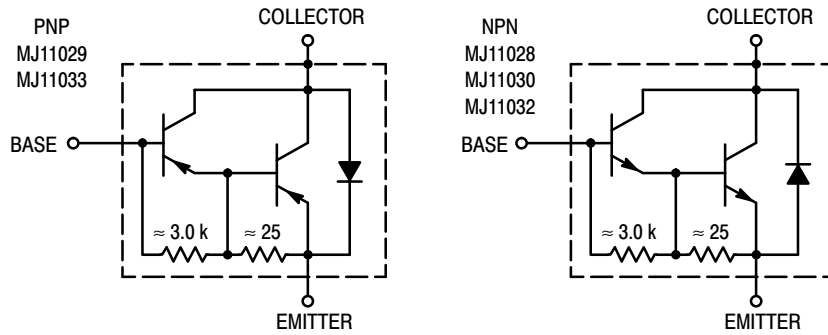


Figure 1. Darlington Circuit Schematic

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 1) ($I_C = 1\text{ mA dc}$, $I_B = 0$)	MJ11028, MJ11029 MJ11030 MJ11032, MJ11033	$V_{(BR)CEO}$	60 90 120	– – – Vdc
Collector–Emitter Leakage Current ($V_{CE} = 60\text{ Vdc}$, $R_{BE} = 1\text{ k}\Omega$) ($V_{CE} = 90\text{ Vdc}$, $R_{BE} = 1\text{ k}\Omega$) ($V_{CE} = 120\text{ Vdc}$, $R_{BE} = 1\text{ k}\Omega$) ($V_{CE} = 60\text{ Vdc}$, $R_{BE} = 1\text{ k}\Omega$, $T_C = 150^\circ\text{C}$) ($V_{CE} = 120\text{ Vdc}$, $R_{BE} = 1\text{ k}\Omega$, $T_C = 150^\circ\text{C}$)	MJ11028, MJ11029 MJ11030 MJ11032, MJ11033 MJ11028, MJ11029 MJ11032, MJ11033	I_{CER}	– – – – –	2 2 2 10 10 mAdc
Emitter Cutoff Current ($V_{BE} = 5\text{ Vdc}$, $I_C = 0$)		I_{EBO}	–	5 mAdc
Collector–Emitter Leakage Current ($V_{CE} = 50\text{ Vdc}$, $I_B = 0$)		I_{CEO}	–	2 mAdc
ON CHARACTERISTICS (Note 1)				
DC Current Gain ($I_C = 25\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$) ($I_C = 50\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$)		h_{FE}	1 k 400	18 k – –
Collector–Emitter Saturation Voltage ($I_C = 25\text{ Adc}$, $I_B = 250\text{ mAdc}$) ($I_C = 50\text{ Adc}$, $I_B = 500\text{ mAdc}$)		$V_{CE(sat)}$	– –	2.5 3.5 Vdc
Base–Emitter Saturation Voltage ($I_C = 25\text{ Adc}$, $I_B = 200\text{ mAdc}$) ($I_C = 50\text{ Adc}$, $I_B = 300\text{ mAdc}$)		$V_{BE(sat)}$	– –	3.0 4.5 Vdc

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

MJ11028, MJ11030, MJ11032 (NPN)

ORDERING INFORMATION

Device	Package	Shipping
MJ11028	TO-204	100 Units / Tray
MJ11028G	TO-204 (Pb-Free)	
MJ11029	TO-204	
MJ11029G	TO-204 (Pb-Free)	
MJ11030	TO-204	
MJ11030G	TO-204 (Pb-Free)	
MJ11032	TO-204	
MJ11032G	TO-204 (Pb-Free)	
MJ11033	TO-204	
MJ11033G	TO-204 (Pb-Free)	

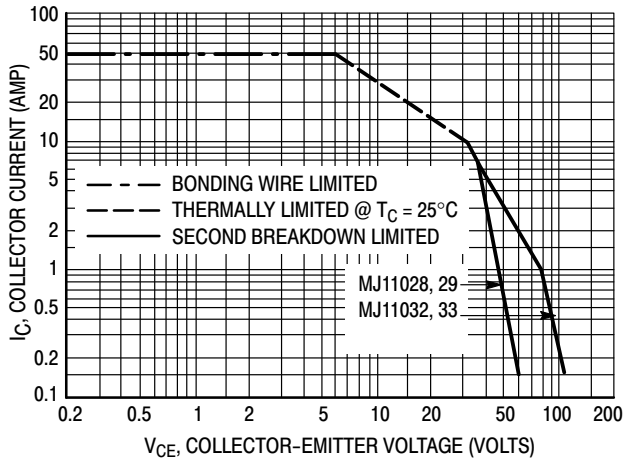


Figure 2. DC Safe Operating Area

There are two limitations on the power-handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_{J(pk)} = 200^\circ\text{C}$; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

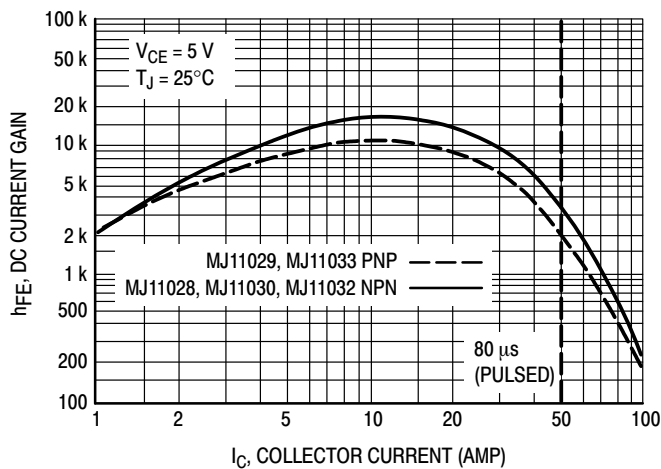


Figure 3. DC Current Gain

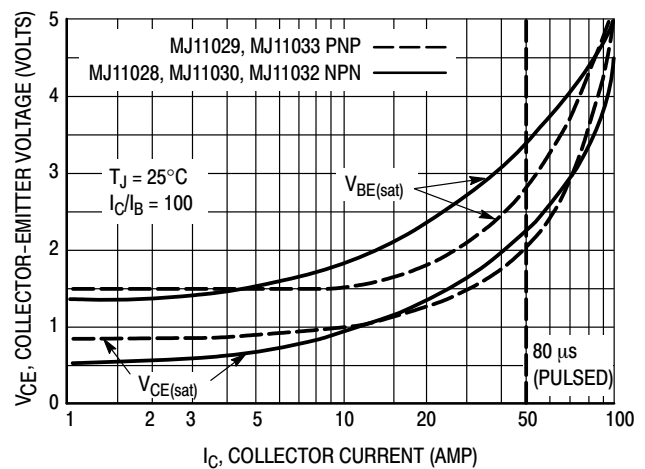
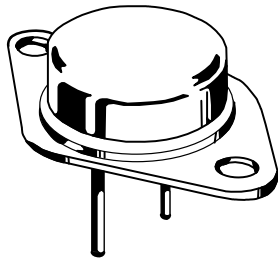


Figure 4. "On" Voltage

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

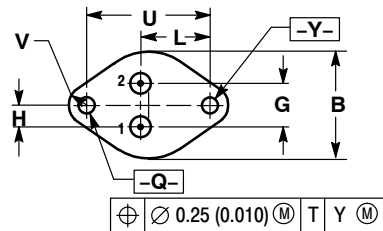
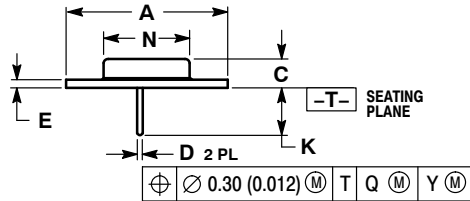
ON Semiconductor®



SCALE 1:1

TO-204 (TO-3)
CASE 197A-05
ISSUE K

DATE 21 FEB 2000



STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

STYLE 2:
PIN 1. EMITTER
2. BASE
CASE: COLLECTOR

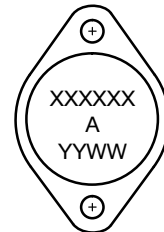
STYLE 3:
PIN 1. GATE
2. SOURCE
CASE: DRAIN

STYLE 4:
PIN 1. ANODE = 1
2. ANODE = 2
CASE: CATHODES

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.530 REF		38.86 REF	
B	0.990	1.050	25.15	26.67
C	0.250	0.335	6.35	8.51
D	0.057	0.063	1.45	1.60
E	0.060	0.070	1.53	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	0.760	0.830	19.31	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
YY = Year
WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking.

DOCUMENT NUMBER:	98ASB42128B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
STATUS:	ON SEMICONDUCTOR STANDARD	
NEW STANDARD:		
DESCRIPTION:	TO-204 (TO-3)	PAGE 1 OF 2

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

